



60V Dual N-Channel MOSFETs

General Description

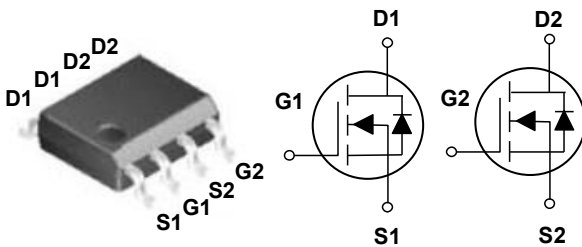
These N-Channel enhancement mode power field effect transistors are using trench MOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BV_{DSS}	$R_{DS(ON)}$	I_D
60 V	54 mΩ	4.5 A

Features

- $R_{DS(ON)} \leq 54m\Omega @ V_{GS}=10V$
- Improved dv/dt Capability
- Fast Switching
- Green Device Available

SOP-8 Pin Configuration



Applications

- Motor Drive
- Power Tools
- LED Lighting

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current - Continuous ($T_C=25^\circ C$)	4.5	A
I_{DM}	Drain Current - Pulsed (NOTE 1)	18	A
EAS	Single Pulse Avalanche Energy (NOTE 2)	11.25	mJ
IAS	Single Pulse Avalanche Current (NOTE 2)	15	A
P_D	Power Dissipation ($T_A=25^\circ C$)	2.1	W
T_J	Operating Junction Temperature Range	-50 to 150	$^\circ C$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ C$
Marking Code		DS6810	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	60	$^\circ C/W$

**60V Dual N-Channel MOSFETs****Electrical Characteristics (T_J=25°C, unless otherwise noted)****Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =60V, V _{GS} =0V	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =5A	---	---	54	mΩ
		V _{GS} =4.5V, I _D =3A	---	---	63	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.5	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =10A	---	6.5	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q _g	Total Gate Charge	V _{DS} =48V, V _{GS} =10V, I _D =4A	---	14	---	nC
Q _{gs}	Gate-Source Charge		---	2.9	---	
Q _{gd}	Gate-Drain Charge		---	2.4	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =6Ω, I _D =4A	---	14	---	nS
T _r	Rise Time		---	4	---	
T _{d(off)}	Turn-Off Delay Time		---	32	---	
T _f	Fall Time		---	2	---	
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1MHz	---	835	---	pF
C _{oss}	Output Capacitance		---	69	---	
C _{rss}	Reverse Transfer Capacitance		---	40	---	
R _g	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	1.7	---	Ω

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	4.5	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A	---	---	1	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =1A, di/dt=100A/us	---	14.6	---	nS
Q _{rr}	Reverse Recovery Charge		---	6.6	---	nC

NOTES :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=15A, R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



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Characteristics Curves

Fig.1 I_D vs. T_C

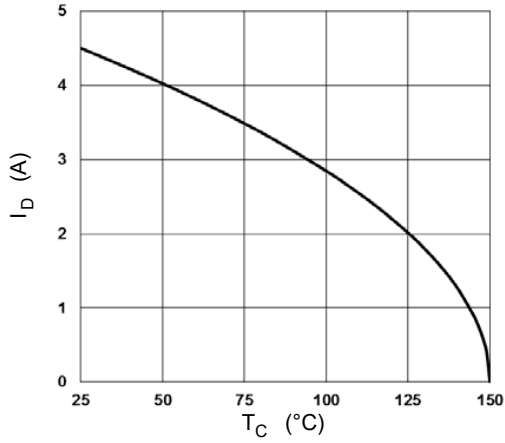


Fig.2 Normalized $R_{DS(ON)}$ vs. T_J

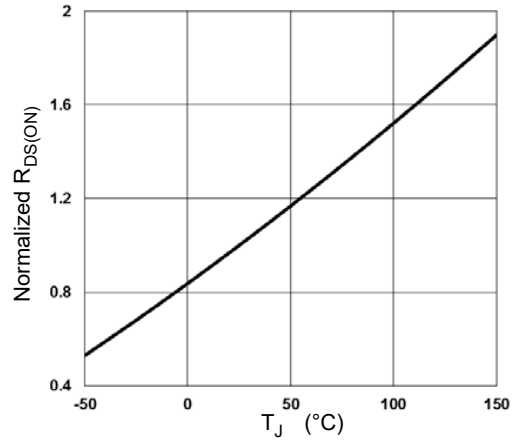


Fig.3 Normalized V_{th} vs. T_J

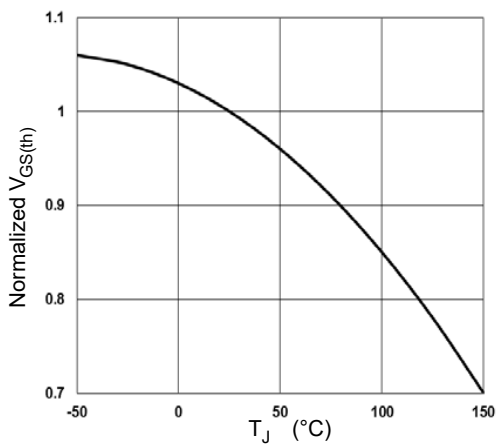


Fig.4 Gate Charge Waveform

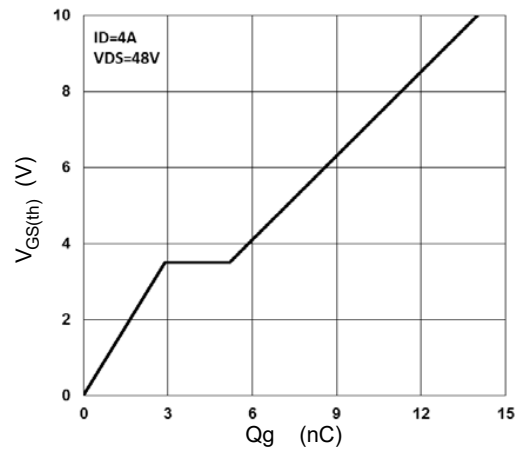


Fig.5 Normalized Transient Response

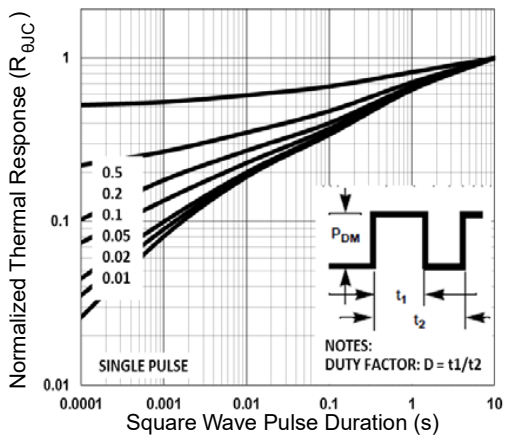
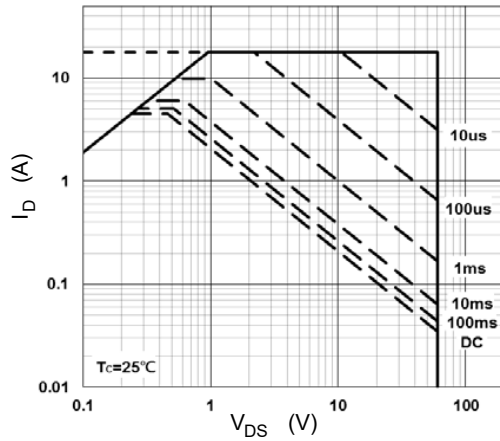


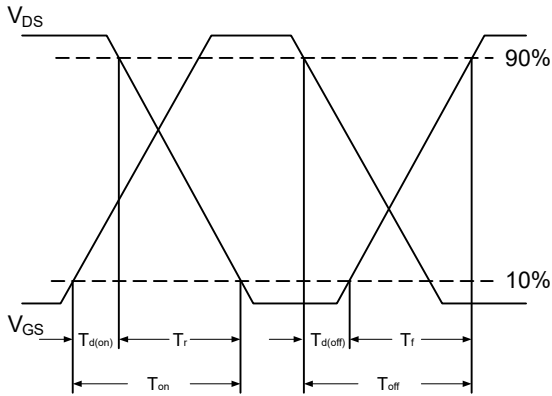
Fig.6 Maximum Safe Operation Area



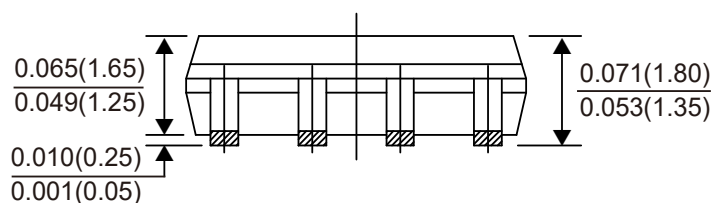
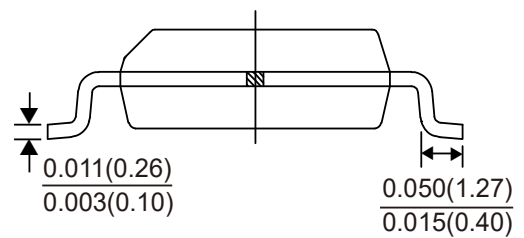
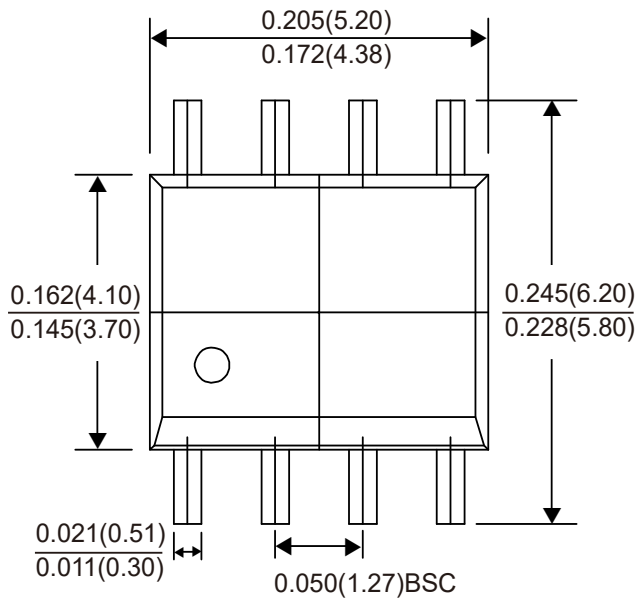


Characteristics Curves

Fig.7 Switching Time Waveform



Package Outline Dimensions



SOP-8

Dimensions in inches and (millimeters)



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